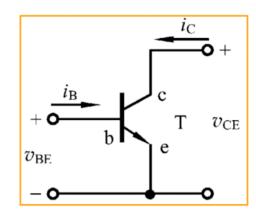


$$\begin{split} &i_{C} = I_{S} \left( e^{(\upsilon_{BE}/V_{T})} - 1 \right) = \frac{A_{E}qD_{n}n_{i}^{2}}{N_{B}W_{B}} \left( e^{(\upsilon_{BE}/V_{T})} - 1 \right) \\ &\approx \frac{A_{E}qD_{n}n_{i}^{2}}{N_{B}W_{B}} e^{(\upsilon_{BE}/V_{T})} \end{split}$$

$$\begin{split} i_{\scriptscriptstyle B} &= \left(\frac{A_{\scriptscriptstyle E} q D_{\scriptscriptstyle p} n_{\scriptscriptstyle i}^2}{N_{\scriptscriptstyle D} L_{\scriptscriptstyle p}} + \frac{A_{\scriptscriptstyle E} q W n_{\scriptscriptstyle i}^2}{2 \tau_{\scriptscriptstyle b} N_{\scriptscriptstyle A}}\right) \left(e^{^{({\scriptscriptstyle \mathcal{V}_{\scriptscriptstyle BE}}/\!\!\!\!/_{\!\!\!\!V_{\scriptscriptstyle T}})}} - 1\right) \\ &\approx \left(\frac{A_{\scriptscriptstyle E} q D_{\scriptscriptstyle p} n_{\scriptscriptstyle i}^2}{N_{\scriptscriptstyle D} L_{\scriptscriptstyle p}} + \frac{A_{\scriptscriptstyle E} q W n_{\scriptscriptstyle i}^2}{2 \tau_{\scriptscriptstyle b} N_{\scriptscriptstyle A}}\right) e^{^{({\scriptscriptstyle \mathcal{V}_{\scriptscriptstyle BE}}/\!\!\!\!/_{\!\!\!\!V_{\scriptscriptstyle T}})}} \end{split}$$



Current gain

$$\beta = \frac{i_C}{i_B}$$

$$i_{B} = \frac{i_{C}}{\beta} = \frac{I_{S} \left( e^{(\upsilon_{BE}/V_{T})} - 1 \right)}{\beta} = \left( \frac{I_{S}}{\beta} \right) \left( e^{(\upsilon_{BE}/V_{T})} - 1 \right)$$



According to KCL:

$$\begin{array}{c|c}
 & i_{\text{C}} \\
+ & & c \\
v_{\text{BE}} \\
- & & e
\end{array}$$

$$i_{E} = i_{B} + i_{C} = \frac{i_{C}}{\beta} + i_{C}$$

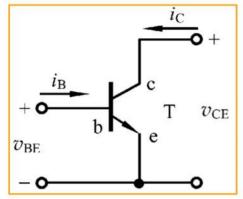
$$= \frac{\beta + 1}{\beta} i_{C}$$

$$= \frac{\beta + 1}{\beta} I_{S} \left( e^{(\upsilon_{BE}/V_{T})} - 1 \right)$$

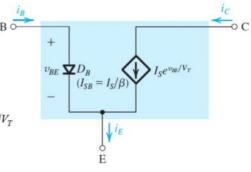
$$\alpha = \frac{i_C}{i_E}$$
  $\longrightarrow$   $\alpha = \frac{\beta}{\beta + 1}$  or  $\beta = \frac{\alpha}{1 - \alpha}$ 

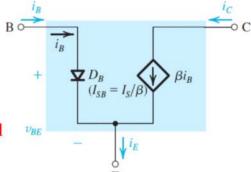
7

Simple bipolar transistor model



$$i_{B} = \frac{i_{C}}{\beta} = \frac{i_{S}}{\beta} e^{v_{BE}/V_{T}}$$

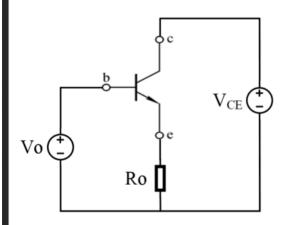




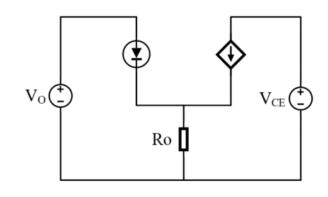
Application of a simple bipolar transistor model

M

Application of a simple bipolar transistor model



Vo = 5V, V<sub>CE</sub> = 12V, Ro = 100 Ω 
$$I_S = 5 \times 10^{-16} A$$



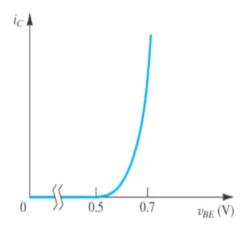
$$V_o = V_{BE} + R_o \cdot I_E \approx V_T \ln \frac{I_C}{I_S} + R_o \cdot I_C$$

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## Concept of transconductance:



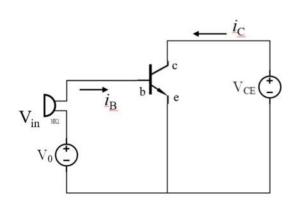
$$g_{m} = \frac{\Delta i_{c}}{\Delta \nu_{BE}} = \frac{di_{c}}{d\nu_{BE}}$$

$$i_c = I_S e^{v_{BE}/V_T}$$

$$g_m = \frac{d}{d\nu_{RE}} \left( I_S e^{\nu_{BE}/V_T} \right) = \frac{I_S}{V_T} e^{\nu_{BE}/V_T} = \frac{i_c}{V_T}$$



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$$V_{in} = V_{m} \sin \omega t$$

$$i_{C} = I_{S}e^{\frac{\left(\frac{V_{0}+V_{im}}{V_{T}}\right)}{V_{T}}} = I_{S}e^{\frac{\left(\frac{V_{0}}{V_{T}}\right)}{V_{T}}} \cdot e^{\frac{\left(\frac{V_{m}\sin\omega t}{V_{T}}\right)}{V_{T}}}$$

$$= I_{CO} \cdot e^{\frac{\left(\frac{V_{m}\sin\omega t}{V_{T}}\right)}{V_{T}}}$$

$$= I_{CO} + \frac{I_{CO}}{V_{T}}V_{m}\sin\omega t$$

$$= I_{CO} + g_{m}V_{m}\sin\omega t$$

$$= I_{CO} + g_{m}V_{m}\sin\omega t$$

## slide 6:

To figure out the component over Now, we need to find out the telationship between it and Note in this circuit branch.

## slide 7:

we know that:

therefore, the component over Use is a produce.

## 5/12/13:

When a small perturbation is added in the input side:

$$I_c = I_s \exp \left( (V_o + V_i o) / V_T \right) = I_s \exp \left( \frac{V_o v_T}{v_T} \right) \cdot \exp \left( \frac{V_o s_{in} w_t}{v_T} \right)$$

1. A bipolar transistor has a collector current of 1mA and  $I_s$ = 5 ×10<sup>-16</sup> A, how much is  $V_{BE}$ ? If  $\beta$  = 50, how much is base current?

1 
$$c = I_{MA}$$
,  $I_{S} = 5 \times 10^{-16} A$   $V_{T} = 26 mV$ 
 $i_{C} = I_{S} \exp \frac{V_{EE}}{V_{T}}$ 
 $V_{BE} = [S \times 178 mV] = 3.89 \text{ We should have an forestory}$ 
 $i_{D} = \frac{i_{C}}{G} = \frac{I_{MA}}{50} = 20 \mu A$ 

